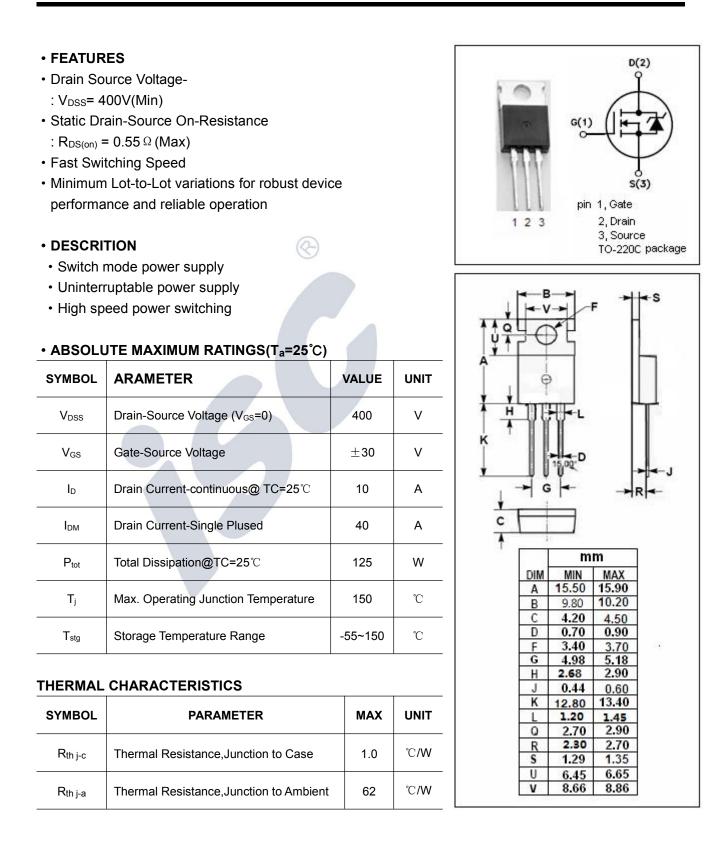


INCHANGE SEMICONDUCTOR

isc N-Channel MOSFET Transistor

IRF740



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isc N-Channel MOSFET Transistor

IRF740

ELECTRICAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	МАХ	UNIT
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0; I _D =0.25mA	400			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} ; I _D =0.25mA	2.0		4.0	V
V _{SD}	Diode Forward On-voltage	I _S = 10A ;V _{GS} = 0			2.0	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} = 10V; I _D = 6A			0.55	Ω
I _{GSS}	Gate-Body Leakage Current	V _{GS} = ±30V;V _{DS} = 0			±100	nA
ldss	Zero Gate Voltage Drain Current	V _{DS} =400V; V _{GS} = 0			25	μA



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